

N-channel LFPAK 80 V 18 mΩ standard level MOSFET

Rev. 02 — 28 October 2010

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters

1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

characteristicsLFPAK provides maximum power density in a Power SO8 package

nexperia

Improved mechanical and thermal

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	80	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; see <u>Figure 1</u>	-	-	45	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	89	W
Tj	junction temperature		-55	-	175	°C
Static characteristics						
R _{DSon} drain-source on-state resistance	V_{GS} = 10 V; I _D = 5 A; T _j = 100 °C; see <u>Figure 12</u>	-	-	28	mΩ	
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } Figure 12;$ see Figure 13	-	15	18	mΩ

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Table 1.	Quick reference datac	ontinued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic	characteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A};$	-	6	-	nC
Q _{G(tot)}	total gate charge	V _{DS} = 40 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	26	-	nC
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy		-	-	64	mJ

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source	mb	
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	mbb076 S
			SOT669 (LFPAK)	

3. Ordering information

Table 3.	Ordering in	formation		
Type num	ber	Package		
		Name	Description	Version
PSMN018-	-80YS	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	80	V
V _{DGR}	drain-gate voltage	T _j ≥ 25 °C; T _j ≤ 175 °C; R _{GS} = 20 kΩ	-	80	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	-	32	А
		V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	-	45	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3	-	182	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	89	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-drain	n diode				
I _S	source current	T _{mb} = 25 °C	-	45	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	182	А
Avalanche r	uggedness				
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \text{ V}; \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{I}_{\text{D}} = 45 \text{ A}; \\ V_{sup} \leq 80 \text{ V}; \text{R}_{GS} = 50 \Omega; \text{ unclamped} \end{array} $	-	64	mJ

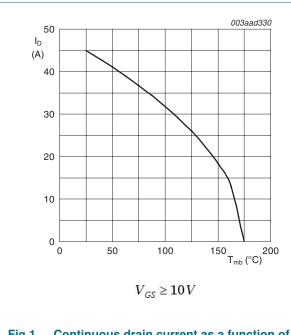
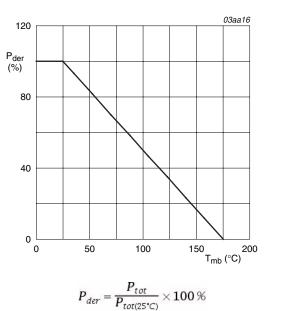
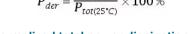


Fig 1. Continuous drain current as a function of mounting base temperature

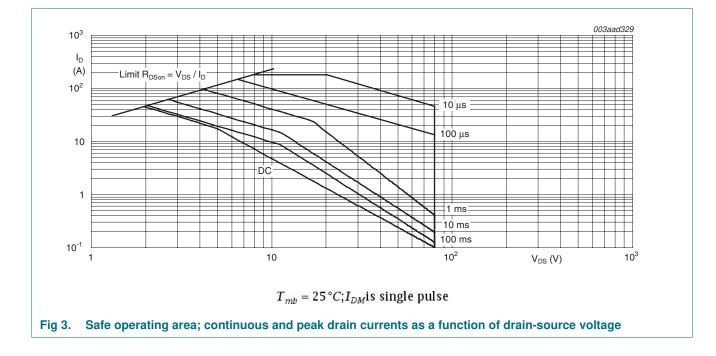






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Р

10⁻¹

tp

Т

t_p (s)

 $\delta = \frac{tp}{T}$

t

1

5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 4	-	0.81	1.7	K/W
1				<i>c</i>	03aad328	
Z _{th(j-mb)} (K/W)	$\delta = 0.5$					

П

10⁻³

Transient thermal impedance from junction to mounting base as a function of pulse duration

10⁻²

Table 5.Thermal characteristics

0.2

0.1

0.05

0.02

single shot

10⁻⁵

10⁻⁴

10⁻¹

10⁻²

Fig 4.

6. Characteristics

Table 6. Characteristics

Tested to JEDEC standards where applicable.

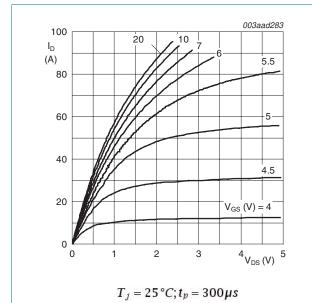
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	73	-	-	V
	voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$	80	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 10</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see Figure 10	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 10</u>	2	3	4	V
I _{DSS} drain le	drain leakage current	V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 °C	-	-	2	μA
		V_{DS} = 80 V; V_{GS} = 0 V; T_j = 125 °C	-	-	50	μA
I _{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 5 A; T _j = 175 °C; see <u>Figure 12</u>	-	-	43	mΩ
	$V_{GS} = 10 \text{ V}; \text{ I}_{D} = 5 \text{ A}; \text{ T}_{j} = 100 ^{\circ}\text{C};$ see Figure 12	-	-	28	mΩ	
	V_{GS} = 10 V; I_D = 5 A; T_j = 25 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	15	18	mΩ	
R _G	internal gate resistance (AC)	f = 1 MHz	-	0.56	-	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	23	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$	-	26	-	nC
Q _{GS}	gate-source charge	see <u>Figure 14;</u> see <u>Figure 15</u>	-	8	-	nC
Q _{GS(th)}	pre-threshold gate-source charge		-	4.7	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	3.3	-	nC
Q _{GD}	gate-drain charge		-	6	-	nC
V _{GS(pl)}	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; \text{ see } \frac{\text{Figure}}{14}; \text{ see } \frac{\text{Figure } 15}{15}$	-	4.8	-	V
C _{iss}	input capacitance	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	1640	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	170	-	pF
C _{rss}	reverse transfer capacitance		-	95	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 40 \text{ V}; \text{ R}_{L} = 1.6 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	16	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	8	-	ns
t _{d(off)}	turn-off delay time		-	30	-	ns
t _f	fall time		-	7	-	ns

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Table 6. Characteristics ...continued

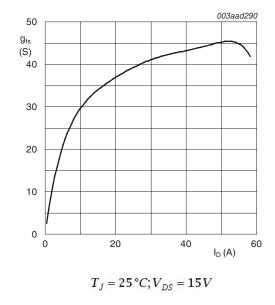
Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drai						
V_{SD}	source-drain voltage	I _S = 5 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 17</u>	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 40 \text{ A}; \text{ d}I_{S}/\text{d}t = 100 \text{ A}/\mu\text{s};$	-	50	-	ns
Qr	recovered charge	$V_{GS} = 0 V; V_{DS} = 40 V$	-	80	-	nC

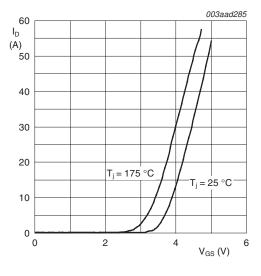






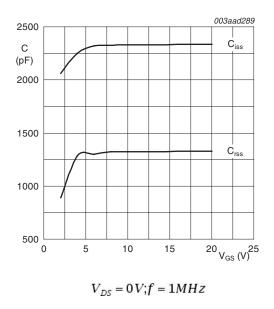








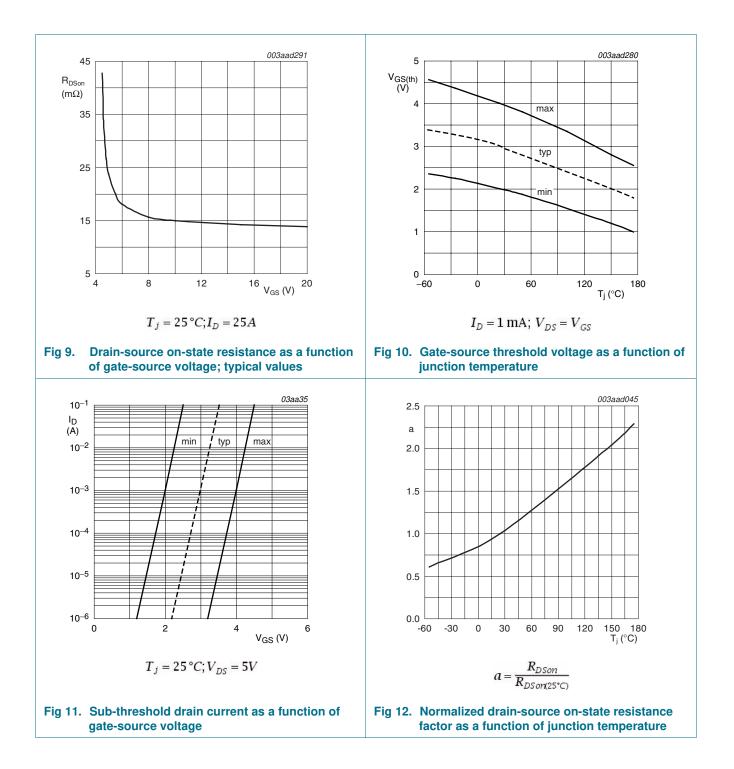




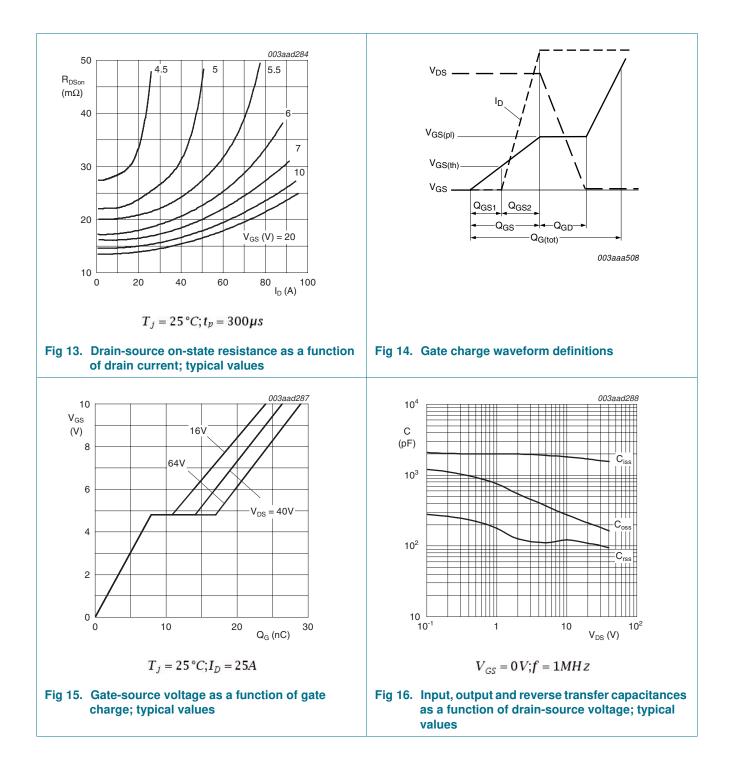


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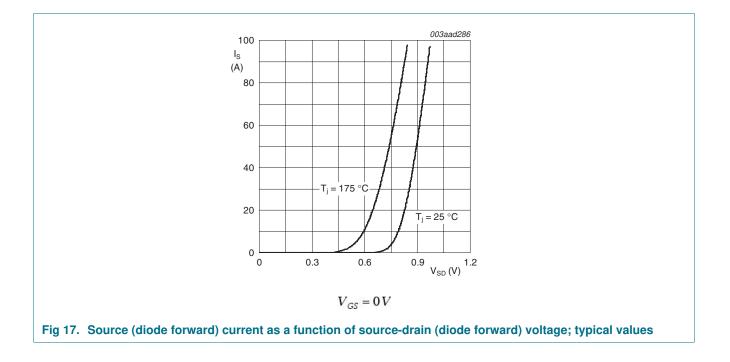
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7. Package outline

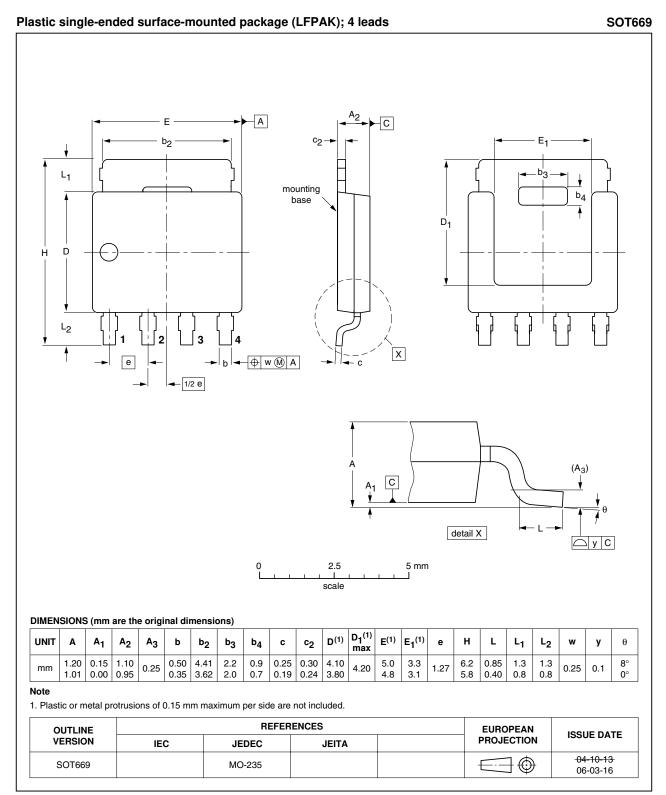


Fig 18. Package outline SOT669 (LFPAK)

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PSMN018-80YS

8. Revision history

Table 7.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN018-80YS v.2	20101028	Product data sheet	-	PSMN018-80YS v.1
Modifications:	 Various changes 	to content.		
PSMN018-80YS v.1	20101026	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <u>http://www.nexperia</u>.com.

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